

TOSHIBA Transistor
Silicon PNP Epitaxial Type (PCT process) Silicon NPN Epitaxial Type (PCT process)

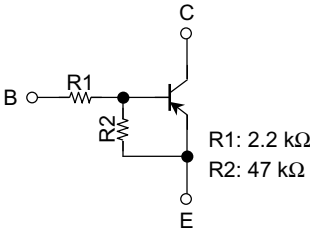
RN49A1

Switching, Inverter Circuit, Interface Circuit
and Driver Circuit Applications.

- Including two devices in US6 (ultra super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

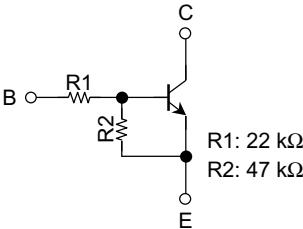
Equivalent Circuit and Bias Resistor Values

Q1



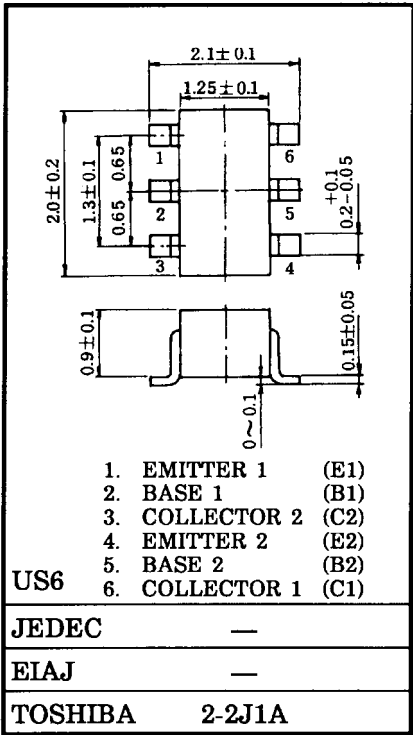
Q1: RN2105F

Q2

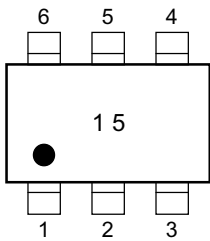


Q2: RN1108F

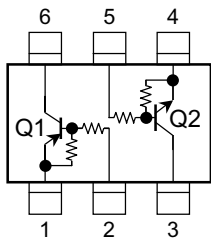
Unit in mm



Marking
Circuit (top view)



Equivalent



961001EAA1

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Q1 Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	–50	V
Collector-emitter voltage	V _{CEO}	–50	V
Emitter-base voltage	V _{EBO}	–5	V
Collector current	I _C	–100	mA

Q2 Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	7	V
Collector current	I _C	100	mA

Q1, Q2 Common Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector power dissipation	P _C (Note)	200	mW
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	–55 to 150	°C

Note: Total rating

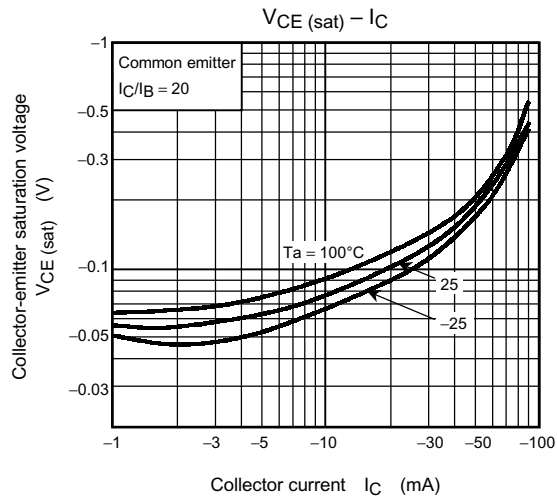
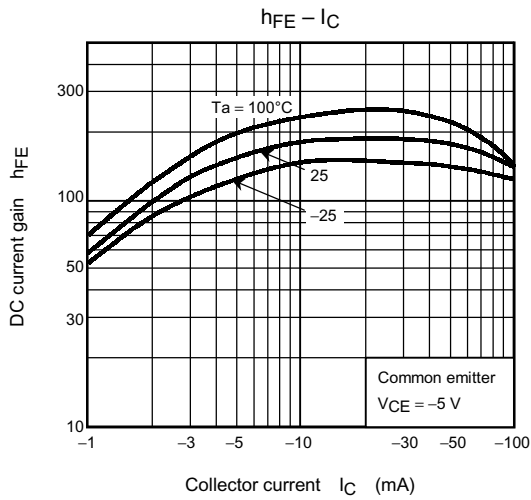
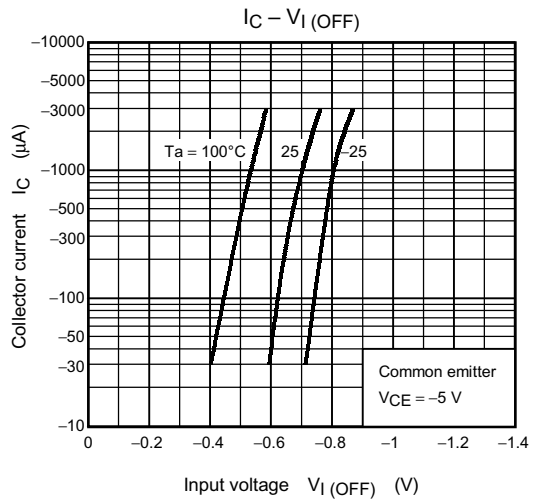
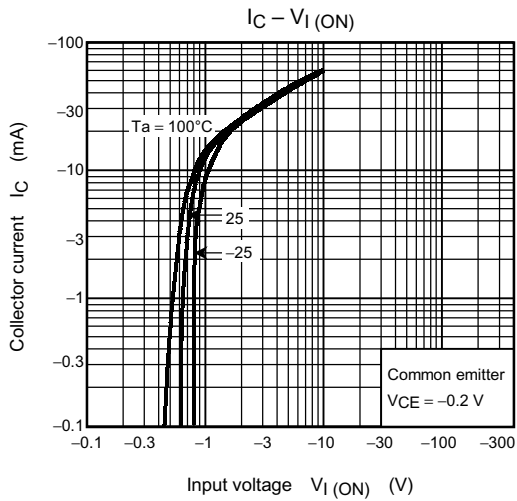
Q1 Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-100	nA
	I_{CEO}	$V_{CE} = -50\text{ V}, I_B = 0$	—	—	-500	
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	-0.078	—	-0.145	mA
DC current gain	h_{FE}	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	80	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -5\text{ mA}, I_B = -0.25\text{ mA}$	—	-0.1	-0.3	V
Input voltage (ON)	$V_I(ON)$	$V_{CE} = -0.2\text{ V}, I_C = -5\text{ mA}$	-0.6	—	-1.1	V
Input voltage (OFF)	$V_I(OFF)$	$V_{CE} = -5\text{ V}, I_C = -0.1\text{ mA}$	-0.5	—	-0.8	V
Transition frequency	f_T	$V_{CE} = -10\text{ V}, I_C = -5\text{ mA}$	—	200	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	3	6	pF
Input resistor	R1	—	1.54	2.2	2.86	kΩ
Resistor ratio	R1/R2	—	0.0421	0.0468	0.0515	

Q2 Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 50\text{ V}, I_E = 0$	—	—	100	nA
	I_{CEO}	$V_{CE} = 50\text{ V}, I_B = 0$	—	—	500	
Emitter cut-off current	I_{EBO}	$V_{EB} = 7\text{ V}, I_C = 0$	0.078	—	0.145	mA
DC current gain	h_{FE}	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$	80	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 5\text{ mA}, I_B = 0.25\text{ mA}$	—	0.1	0.3	V
Input voltage (ON)	$V_I(ON)$	$V_{CE} = 0.2\text{ V}, I_C = 5\text{ mA}$	1.0	—	2.6	V
Input voltage (OFF)	$V_I(OFF)$	$V_{CE} = 5\text{ V}, I_C = 0.1\text{ mA}$	0.6	—	1.16	V
Transition frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 5\text{ mA}$	—	250	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	3	6	pF
Input resistor	R1	—	15.4	22	28.6	kΩ
Resistor ratio	R1/R2	—	0.421	0.468	0.515	

Q1



Q2

